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View Online at https://aerobasegroup.com/nsn/5961-01-090-3257

Inclosure Material:

Metal

Overall Length:

1.252 inches

Overall Height:

0.340 inches

Overall Width:

0.700 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-66

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

90.0 collector to base voltage, dc and 80.0 collector to emitter voltage/static/base open and 5.0 emitter to base voltage, dc

Current Rating Per Characteristic:

Between 1.00 amperes source cutoff current and 3.00 amperes source cutoff current

Power Rating Per Characteristic:

35.0 watts small-signal input power, common-collector absolute

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Test Data Document:

81755-c8751 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

1 case and 2 pin

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

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